

# STPSC4H065

### 650 V power Schottky silicon carbide diode

#### Datasheet – production data

### Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- High forward surge capability

### Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide bandgap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode will boost the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

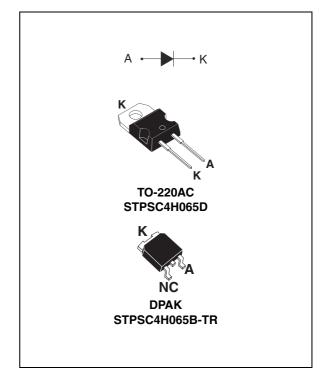


Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	4 A
V <sub>RRM</sub>	650 V
T <sub>j</sub> (max)	175 °C

This is information on a product in full production.

### 1 Characteristics

#### Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Par	Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage		650	V
I <sub>F(RMS)</sub>	Forward rms current		22	А
I <sub>F(AV)</sub>	Average forward current $\delta = 0.5$	T <sub>c</sub> = 135 °C	4	А
		$t_p = 10 \text{ ms sinusoidal}, T_c = 25 \text{ °C}$	38	
I <sub>FSM</sub>	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}, T_c = 125 \text{ °C}$	35	А
		$t_p = 10 \ \mu s \ square, \ T_c = 25 \ ^\circ C$	200	
I <sub>FRM</sub>	Repetitive peak forward current	$T_{c} = 135 \ ^{\circ}C, T_{j} = 150 \ ^{\circ}C, \delta = 0.1$	11	А
T <sub>stg</sub>	Storage temperature range		-55 to +175	°C
Тj	Operating junction temperature <sup>(1)</sup>		-40 to +175	°C

1.  $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$  condition to avoid thermal runaway for a diode on its own heatsink

#### Table 3.Thermal resistance (typical values)

Symbol	Parameter	Va	Unit	
Symbol	Farameter	Тур.	Max.	onn
R <sub>th(j-c)</sub>	Junction to case	1.8	2.7	°C/W

#### Table 4. Static electrical characteristics

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
I <sub>B</sub> <sup>(1)</sup>	) Reverse leakage current $T_j = 2$		V _V	-	3	40	
'R ` ´	IR ( ) neverse leakage current	T <sub>j</sub> = 150 °C	$V_{R} = V_{RRM}$	-	35	170	μA
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 4 A	-	1.56	1.75	V
V <sub>F</sub> (2)	Forward voltage drop	$T_j = 150 \ ^\circ C$		-	1.98	2.5	v

1.  $t_p = 10 \text{ ms}, \delta < 2\%$ 

2.  $t_p = 500 \ \mu s, \ \delta < 2\%$ 

To evaluate the conduction losses use the following equation: P = 1.35 x  $I_{F(AV)}$  + 0.288 x  $I_{F}^{2}_{(RMS)}$ 

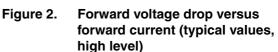
Table 5.Dynamic electrical characteristics

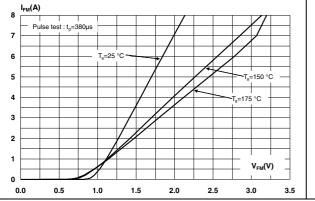
Symbol	Parameter	Test conditions	Min.	Тур.	Unit
Q <sub>cj</sub> <sup>(1)</sup>	Total capacitive charge	V <sub>R</sub> = 400 V		12.5	nC
C	C <sub>j</sub> Total capacitance	$V_R = 0 V$ , $T_c = 25 °C$ , $F = 1 MHz$		200	pF
Uj		$V_{R} = 400 \text{ V}, \text{ T}_{c} = 25 \text{ °C}, \text{ F} = 1 \text{ MHz}$		21	μr

1. Most accurate value for the capacitive charge:  $Q_{cj} = \int_{0}^{V_{OUT}} c_{j}(v_R) dv_R$ 



#### Figure 1. Forward voltage drop versus forward current (typical values, low level)





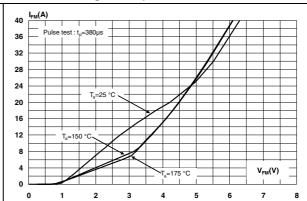


Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

Figure 4. Peak forward current versus case temperature

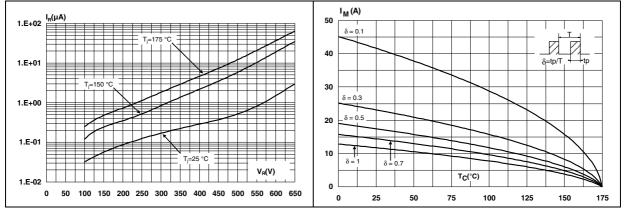
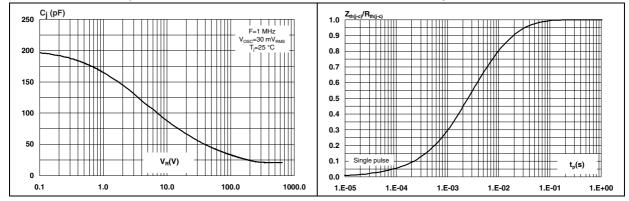
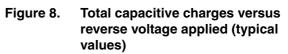


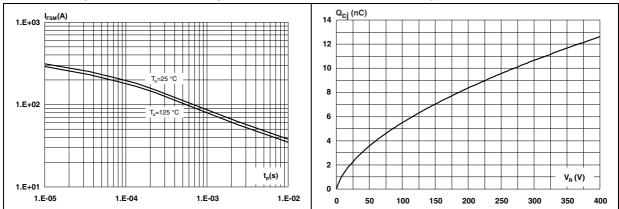
Figure 5. Junction capacitance versus reverse voltage applied (typical values)

Figure 6. Relative variation of thermal impedance junction to case versus pulse duration



#### Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)







57

### 2 Package information

- Epoxy meets UL94, V0
- Recommended torque value (TO-220AC): 0.4 to 0.6 N·m
- Cooling method: conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

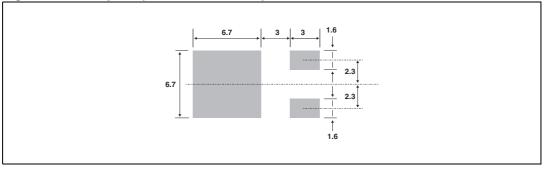
Table 6.TO-220AC dimensions

			Dimer	nsions	
	Ref.	Millin	neters	Inc	hes
		Min.	Max.	Min.	Max.
	А	4.40	4.60	0.173	0.181
H2 A A	С	1.23	1.32	0.048	0.051
ØI → C←	D	2.40	2.72	0.094	0.107
	E	0.49	0.70	0.019	0.027
	F	0.61	0.88	0.024	0.034
	F1	1.14	1.70	0.044	0.066
	G	4.95	5.15	0.194	0.202
	H2	10.00	10.40	0.393	0.409
	L2	16.40 typ.		0.645 typ.	
L4	L4	13.00	14.00	0.511	0.551
F→↓← M⊨	L5	2.65	2.95	0.104	0.116
	L6	15.25	15.75	0.600	0.620
G	L7	6.20	6.60	0.244	0.259
	L9	3.50	3.93	0.137	0.154
	М	2.6	typ.	0.10	2 typ.
	Diam. I	3.75	3.85	0.147	0.151

Table 7. DPAK dimensions						
		Dimensions				
	Ref.	Millim	Millimeters		hes	
		Min.	Max.	Min.	Max.	
	А	2.20	2.40	0.086	0.094	
Ę → A ←	A1	0.90	1.10	0.035	0.043	
	A2	0.03	0.23	0.001	0.009	
	В	0.64	0.90	0.025	0.035	
	B2	5.20	5.40	0.204	0.212	
H R	С	0.45	0.60	0.017	0.023	
	C2	0.48	0.60	0.018	0.023	
	D	6.00	6.20	0.236	0.244	
	Е	6.40	6.60	0.251	0.259	
	G	4.40	4.60	0.173	0.181	
0.60 MIN.	Н	9.35	10.10	0.368	0.397	
v2	L2	0.80	typ.	0.03	1 typ.	
	L4	0.60	1.00	0.023	0.039	
	V2	0°	8°	0°	8°	

Table 7.DPAK dimensions

Figure 9. Footprint (dimensions in mm)





## 3 Ordering information

#### Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPSC4H065D	STPSC4H065D	TO-220AC	1.86 g	50	Tube
STPSC4H065B-TR	STPSC 4H065	DPAK	0.32 g	2500	Tape and reel

### 4 Revision history

#### Table 9.Document revision history

Date	Revision	Changes
31-Aug-2012	1	First issue.
10-Oct-2012	2	Added Max. value in <i>Table 3</i> .



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